PNP/NPN Epitaxial Planar Type Silicon Transistors



2SB1271/2SD1907

High-Current Switching Applications

Applications

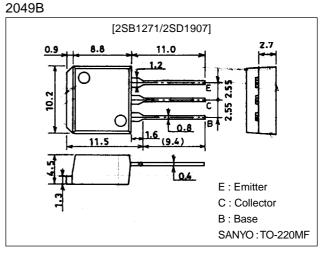
• Suitable for relay drivers, high-speed inverters, converters, and other general high-current switching applications.

Features

- \cdot Suitable for sets whose height is restricted.
- \cdot Low collector to emitter saturation voltage.
- · Large current capacity.

Package Dimensions

unit:mm



():2SB1271

Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		(-)90	V
Collector-to-Emitter Voltage	VCEO		(-)80	V
Emitter-to-Base Voltage	VEBO		(–)6	V
Collector Current	IC		(-)7	Α
Collector Current (Pulse)	ICP		()12	A
Collector Dissipation	PC		1.65	W
		Tc=25°C	40	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector Cutoff Current	I _{CBO}	V _{CB} =(-)80V, I _E =0			(–)0.1	mA
Emitter Cutoff Current	IEBO	V _{EB} =(-)4V, I _C =0			(–)0.1	mA
DC Current Gain	h _{FE} 1	V _{CE} =(-)2V, I _C =(-)1A	70*		280*	
	h _{FE} 2	V _{CE} =(-)2V, I _C =(-)4A	30			
Gain-Bandwidth Product	fT	V _{CE} =(-)5V, I _C =(-)1A		20		MHz
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =(-)4A, I _B =(-)0.4A			0.4	V
					(-0.5)	V

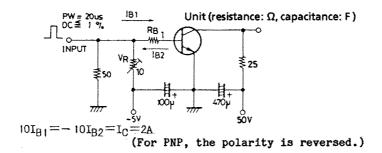
* : The 2SB1271/2SD1907 are classified by 1A h_{FE} as follows : 70 Q 140 100 R 200 140 S 280

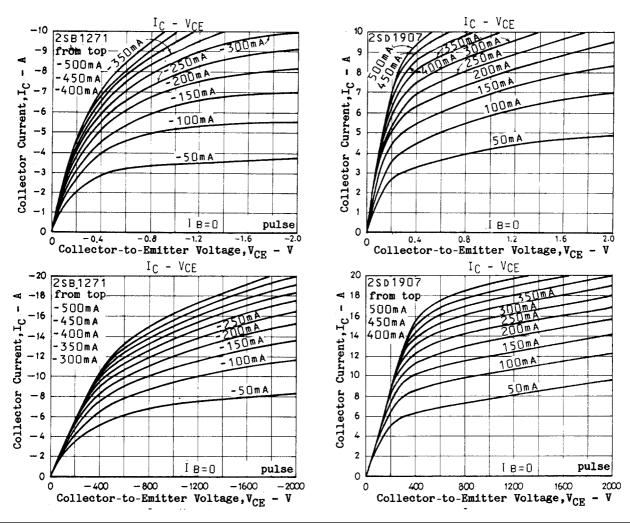
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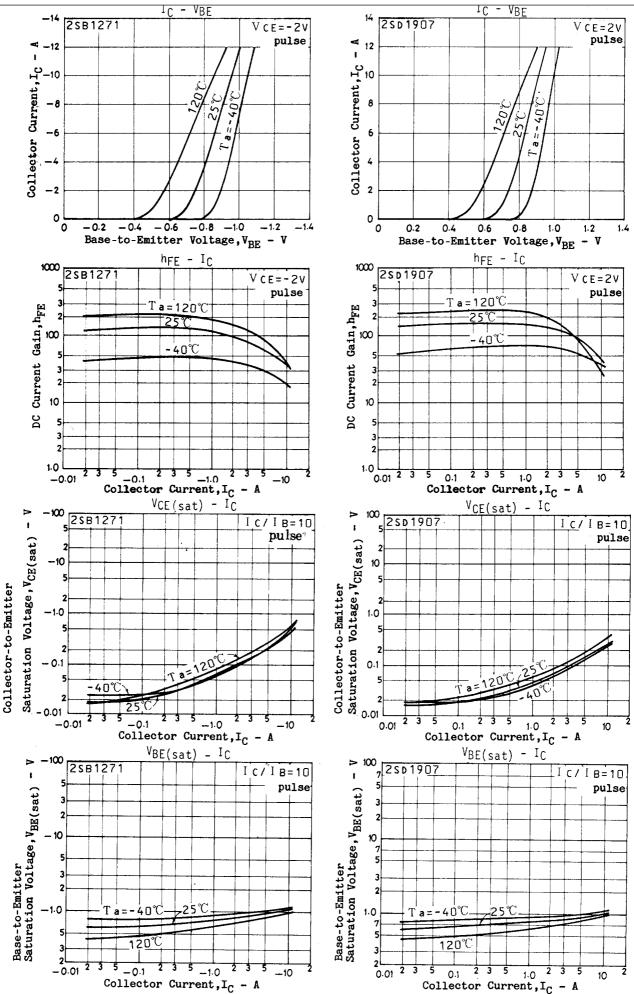
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Parameter	Symbol	Conditions		Ratings		
	Symbol		min	typ	max	Unit
Collector-to-Base Breakdown Voltage	V(BR)CBO	I _C =(-)1mA, I _E =0	(–)90			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I _C =(−)1mA, R _{BE} =∞	(–)80			V
Emitter-to-Base Breakdown Voltage	V _{(BR)EBO}	I _E =(-)1mA, I _C =0	(–)6			V
Turn-ON Time	ton	See specified test circuit.		(0.2)		μs
				0.1		μs
Storage Time	t _{stg}	See specified test circuit.		(0.7)		μs
				1.6		μs
Fall Time	t _f	See specified test circuit.		(0.2)		μs
				0.4		μs

Switching Time Test Circuit



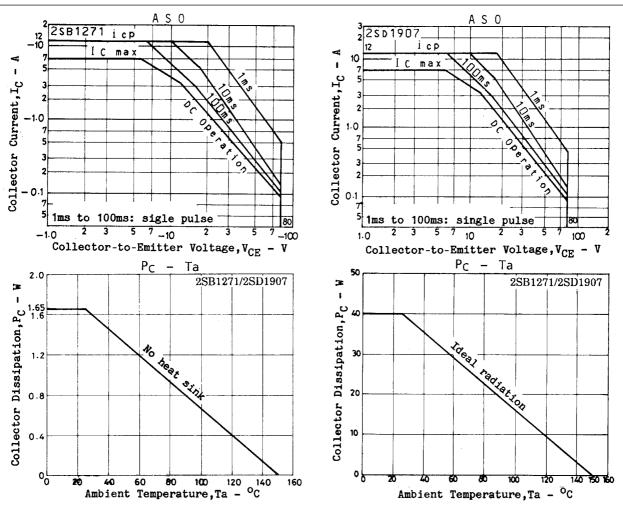




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